

Bound Magnetic Polarons in the 3d-electron Ferromagnetic Spinel Semiconductor CdCr_2Se_4

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Muon spin rotation/relaxation spectroscopy has been employed to study electron localization around a donor center — the positive muon — in the 3d magnetic spinel semiconductor CdCr_2Se_4 at temperatures from 2 to 300 K in magnetic fields up to 7 T. A bound state of an electron around a positive muon — a magnetic polaron — is detected far above the ferromagnetic transition up to 300 K. Electron localization into a magnetic polaron occurs due to its strong exchange interaction with the magnetic 3d electrons of local Cr^{3+} ions, which confines its wave function within $R \approx 0.3$ nm, allowing significant overlap with both the nearest and next nearest shells of Cr ions.

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The semiconductors currently in use as working media in electronics and information technology (Si, Ge, GaAs *etc.*) are nonmagnetic; therefore the spin of the carriers has so far played a minor role in semiconductor devices. One way to enhance spin-related phenomena for semiconductor spintronics applications [1, 2] is to incorporate magnetic ions (typically Mn) into nonmagnetic semiconductors to realize dilute magnetic semiconductors (DMS) [3, 4]. The interplay between electric and magnetic properties in ferromagnetic (FM) Mn-doped III-V DMS has recently been demonstrated [5–7]. Combined with nonmagnetic semiconductors, these DMS may also serve as polarized spin injectors in spintronics devices [8, 9]. The FM in these *p*-type materials results from a long-range coupling between the Mn atoms mediated by holes generated by Mn substitution at the trivalent cation site [10].

Unfortunately, the ferromagnetism in III-V Mn-doped DMS is limited by low concentration of magnetic ions. Molecular beam epitaxy results in a non-equilibrium enhancement of the otherwise low solubility of transition metals in III-V hosts, but still allows incorporation of no more than about 7-8% of Mn atoms; above this critical concentration Mn tends to cluster and phase separate [11]. Even at lower concentrations, spatial homogeneity may be affected by adding Mn [10] and nanoscale-range magnetic inhomogeneities can occur [12].

By contrast, intrinsic magnetic semiconductors (MS) such as the 4f Eu chalcogenides or 3d Cr spinels exhibit spontaneous homogeneous ferromagnetic order without any doping. When doped, these MS show semiconducting behavior (both *n*- and *p*-type), which indicates strong mutual influence between electrical and magnetic properties [13, 14]. Successful demonstration of the epitaxial growth of EuO and CdCr_2Se_4 on technologically im-

portant semiconductors Si, GaN, GaAs and GaP [15–17] makes them very attractive working media for spintronics applications. These materials offer several important advantages over DMS, such as higher magnetization, spatial homogeneity and wider ranges of conductivity tunable by doping. The longer spin lifetimes and spin-scattering lengths of electrons in Si, GaAs and GaN [17–19], as well as much higher electron mobilities compared with those of holes, makes the ability to support *n*-type conductivity in MS especially attractive for semiconductor spintronics.

Since charge and spin transport for electrons in Si, GaAs, GaP and GaN is excellent, the effectiveness of prospective all-semiconductor spintronics devices is determined by the electron transport in doped magnetic semiconductors. These materials, however, can support states that lead to severe electron localization. In fact, MS provide optimal conditions for the formation of a new type of quasiparticle — the *magnetic polaron* (MP) — in which conduction electron “autolocalization” stabilizes an atomic-scale region of the ferromagnetic phase well above T_c [14, 20, 21]. This electron localization in MS profoundly modifies their magnetic, electrical and optical properties. In particular, such MP determine most of the transport properties of magnetic semiconductors, leading to metal-insulator transitions with a remarkable resistivity change of up to 13 orders of magnitude (in doped EuO) and colossal magnetoresistance which suppresses resistivity by 3-4 orders of magnitude in magnetic fields of ~ 10 T [14]. Measurements of both resistivity and Hall effect in the ferromagnetic spinel CdCr_2Se_4 clearly show that these remarkable properties reflect changes in the density, not the mobility, of charge carriers [14]. These effects can be explained in terms of electron localization into entities roughly the size of a unit cell: MP. In fact,

the MP concept now forms the basis for numerous studies of MS and related materials [22].

A magnetic polaron is formed by an electron localized due to its strong exchange interaction J with magnetic ions in its immediate environment, whose direct coupling is rather weak. Of relevance to the current study is the *bound* MP, in which the increase in the kinetic energy of the electron due to localization is compensated by *both* the s - $d(f)$ exchange interaction J and the Coulomb interaction with the corresponding donor, so that the net change in the energy

$$\Delta F = \frac{\hbar^2}{2m^*R^2} - J\frac{a^3}{R^3} - \frac{e^2}{\epsilon R} \quad (1)$$

has a minimum as a function of R — thus determining the radius of the electron confinement [14, 22]. The dominant exchange term is optimized by maximum overlap of the MP electron with nearby magnetic ions.

Magnetic polarons have recently been detected in 4f magnetic semiconductors EuS, EuO, EuSe [23] and SmS [24], following muon spin rotation/relaxation (μ^+ SR) [25] experiments in nonmagnetic semiconductors [26, 27], that revealed the details of electron capture to form a muonium ($\text{Mu} \equiv \mu^+e^-$) atom. Formation and dissociation of Mu more generally models electron capture by and release from donor centers, since a positive muon acts in this respect just like any other Coulomb attractive impurity [28]. In non-magnetic semiconductors, formation of such Mu atoms is driven solely by the Coulomb interaction; in magnetic semiconductors, it is the combined effect of the Coulomb and exchange interactions which drives Mu formation [23, 24].

In treating the s - $d(f)$ exchange interaction, two limiting cases are important: when the s -electron bandwidth W is large compared with J , and when $J \gg W$. The former case is typical for the s - f exchange in rare-earth compounds where the extremely localized f -electrons are screened by electrons of other shells. In particular, in Eu compounds the s -electron delocalized in the rather wide (a few eV) hybridized $5d$ - $6s$ band exchanges with the partially filled inner $4f$ shell, which is separated from the band states by completely filled $5s$ and $6p$ shells, thus reducing J to a few tenths of an eV. The opposite case $W \ll J$ [29] provides the basis for the well-known double exchange in transition metal compounds. Perhaps surprisingly, this inequality is likely to be quite realistic in such compounds where the charge carriers are often of the same d -type as the localized spins of the magnetic ions. In particular, in CdCr_2Se_4 the Fermi level falls in the middle of the narrow d -band which lies just below a much broader unoccupied s - p conduction band [30].

In this Letter, we present experimental evidence of severe electron localization into a magnetic polaron bound to a positive muon in the paramagnetic phase of the 3d-electron magnetic semiconductor CdCr_2Se_4 .

CdCr_2Se_4 is a chalcogenide spinel with cubic symmetry

(56 atoms per unit cell), a lattice constant of 10.72 Å and a direct gap of about 1.5 eV. Its magnetic moment per chemical formula is close to $6 \mu_B$, which corresponds to the sum of two Cr^{3+} moments, each having a moment of $3 \mu_B$. Ordering of the Cr^{3+} moments into the FM phase occurs at $T_c = 130$ K. Above T_c its paramagnetic susceptibility exhibits Curie-Weiss behavior.

Single crystals of CdCr_2Se_4 for the current study were grown by the closed-tube vapor transport technique. They all have perfect octahedral shape with typical sizes of 3-5 mm. They are slightly n -type with carrier concentration of about 10^{18} cm^{-3} at room temperature. Magnetization (SQUID) measurements in $H = 50$ Oe were used to determine $T_c = 130$ K for these crystals, in close agreement with literature data. Time-differential μ^+ SR experiments using 100% spin-polarized positive muons were carried out on the M15 surface muon channel at TRIUMF using the *HiTime* μ^+ SR spectrometer.

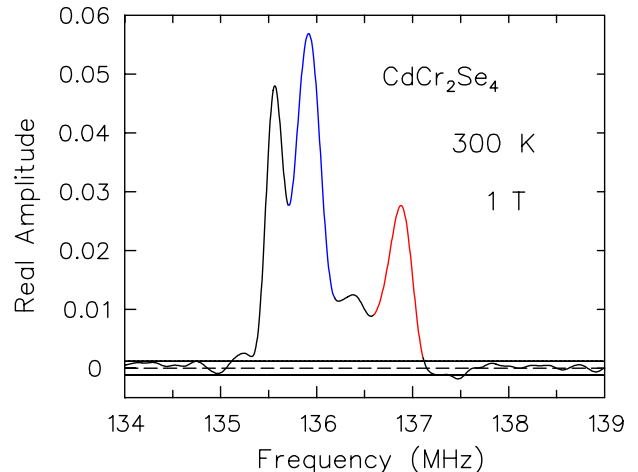


FIG. 1: Frequency spectrum of muon spin precession in CdCr_2Se_4 in a transverse magnetic field of $H = 1$ T at $T = 300$ K. The two-frequency pattern (blue and red online), characteristic of the muon-electron bound state, occurs at frequencies higher than the narrower background signal.

In a high magnetic field applied transverse to the initial muon polarization, the TF- μ^+ SR spectra exhibit two Mu-like signals shifted to higher frequencies relative to the narrow line positioned exactly at the diamagnetic frequency $\nu_\mu = \gamma_\mu B / 2\pi$ (where $\gamma_\mu = 2\pi \times 135.5 \text{ MHz/T}$ is the muon gyromagnetic ratio and B is the magnetic field) as shown in Fig. 1. This narrow line is a background signal from muons stopped outside the sample and provides a good reference since it does not depend on temperature. The two broader signals (blue and red online) at higher frequencies that depend on both temperature and magnetic field present a characteristic signature of the muon-electron bound state. For a μ^+e^- (Mu) spin system [as for p^+e^- (H)] governed by the Breit-Rabi Hamiltonian, these signals correspond to two muon spin-flip transitions between states with fixed electron spin orientation [25].

Accordingly, the rotating reference frame fits of the μ^+ SR spectra in the time domain at various temperatures show 3-frequency precession (1 background and 2

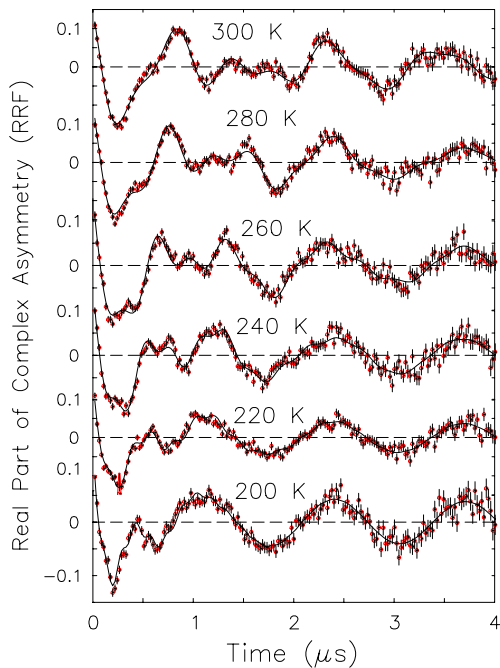


FIG. 2: Time-domain fits of TF- μ SR spectra in the rotating reference frame in a field of $H = 1$ T at different temperatures. Mu-like signals, Fig. 2). The evolution of these signals is presented in the inset to Fig. 3. We claim that the two Mu-like lines are the spectroscopic signature of the magnetic polaron — one electron localized around the positive muon by the combined effects of Coulomb and exchange interactions. In CdCr_2Se_4 this muon-bound MP forms at temperatures well above T_c , up to at least 300 K. The shift of the centroid of the two-line MP spectrum, the splitting and linewidths all scale with the bulk magnetic susceptibility over the 160-300 K temperature range, implying a common origin — magnetic polarons and their orientational dynamics.

Similar 2-frequency signals originating from magnetic polarons are detected in the $4f$ magnetic semiconductors EuS , EuO , EuSe [23] and SmS [24]. In all MS studied, the MP lines are shifted with respect to the reference signal, reflecting the local ferromagnetic environment around the muon. In Eu chalcogenides, the MP lines exhibit negative shifts with respect to the reference signal, indicating that the MP electron spin is opposite to the net polaron spin. Addition of the MP electron effectively reduces the spin of the neighboring Eu ion from $7/2$ (according to Hund’s rule, the maximum allowed spin is for a half-filled f -shell) to 3 due to Pauli exclusion. By contrast, in Cr spinels the MP electron is bound to have its spin parallel to the net MP spin (Hund’s rule for a less than half-filled d -shell), which effectively increases the spin of one of the neighboring Cr ions from its original value of $3/2$ to 2. Accordingly, in CdCr_2Se_4 the FM shift is positive (see Fig. 1). The absolute value of this shift at room temperature and 1 T is about 0.007 T.

The splitting $\Delta\nu$ between the two MP lines provides information on the muon-electron hyperfine coupling A ,

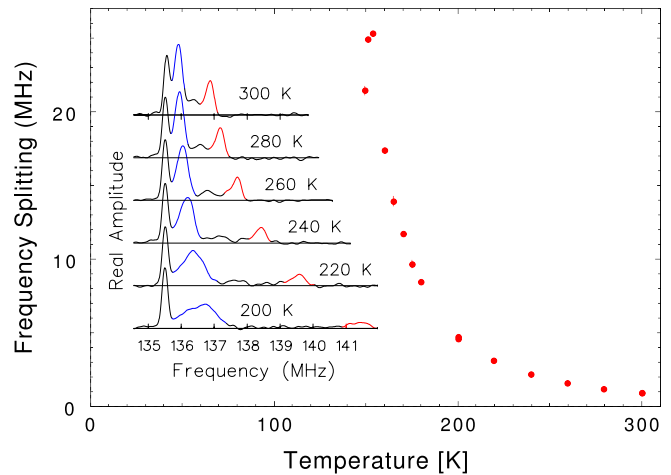


FIG. 3: Temperature dependence of the splitting between MP lines in a magnetic field of $H = 1$ T. The inset shows the evolution of the frequency spectra with temperature.

which is determined by the probability density of the electron wavefunction at the muon [25]. Figure 3 shows the temperature dependence of this splitting. A distinctive feature of magnetic semiconductors in general, and CdCr_2Se_4 in particular, is a strong dependence of the conduction electron energy on the magnetization due to the exchange interaction between the mobile electron and localized $d(f)$ spins, the minimum electron energy being achieved at the ferromagnetic ordering [14]. In the paramagnetic state, an “extra” electron tends to establish and support this ordering, thus forming a FM “droplet” (MP) over the extent of its wave function. The exchange contribution to the localization [see Eq. (1)] amounts to the difference between the paramagnetic disorder of the CdCr_2Se_4 and the enhanced (FM) order in the MP. By contrast, in the FM state the exchange contribution to the localization is negligible, as the lattice spins are already aligned. In fact, as the magnetization develops towards low temperature, the exchange contribution to electron localization diminishes and therefore can no longer compensate the increase of its kinetic energy. The electron thus avoids strong localization as the temperature approaches T_c from above. Accordingly, we do not detect the MP lines below about 150 K (see Fig. 3).

Temperature and magnetic field dependences of the MP signal frequency splitting $\Delta\nu$ provide information on the characteristic size (the localization radius for electron confinement) of the MP in CdCr_2Se_4 . Since the Mu electron spin is “locked” to the MP moment and the experiment samples the component along the applied field, the observed splitting scales with the mean orientation of the MP moment with respect to the external field, reaching the intrinsic Mu hyperfine constant only for complete alignment (see Appendix of Ref.[23]). Amplitudes for the two-frequency spectrum qualitatively scale as expected for a bound electron whose spin is locked to that of the polaron core, providing strong support for this picture. Within a mean field approximation, $\Delta\nu$ is thus propor-

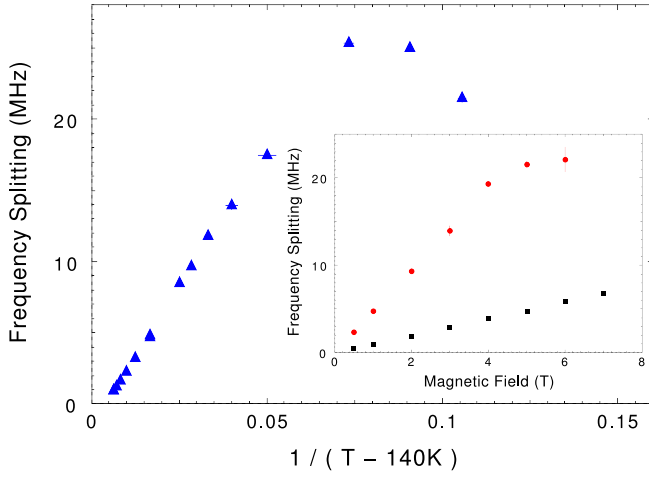


FIG. 4: Dependence of the splitting between MP lines on inverse temperature in a magnetic field of $H = 1 \text{ T}$. Inset: magnetic field dependence of the same splitting at $T = 200 \text{ K}$ (circles) and $T = 300 \text{ K}$ (squares).

tional to a Brillouin function [24, 31]. For $g\mu_B B \ll k_B T$, this is linear in $B/(T - \Theta)$ (see Fig. 4):

$$\Delta\nu = A \left[\frac{g\mu_B B}{3k_B(T - \Theta)} \right] (\mathcal{S} + 1), \quad (2)$$

where $\Theta = 140 \text{ K}$ is the paramagnetic Curie temperature of CdCr_2Se_4 and $\mathcal{S}$ is the net polaron spin. At low $T - \Theta$ and high B , $\Delta\nu$ saturates at a value of A [23–25].

The vacuum state of a Mu atom is characterized by its hyperfine coupling $A_{\text{vac}} = 4463 \text{ MHz}$ which corresponds to electron confinement within $R_{\text{Bohr}} = 0.0529 \text{ nm}$. In a solid nonmagnetic medium, Mu usually has $A < A_{\text{vac}}$ so that, in a magnetic field high enough to satisfy $\gamma_\mu B/2\pi \gg A$, the splitting is $\Delta\nu = A$, independent of temperature and magnetic field [23–25]. Figure 4 shows the MP frequency splitting in CdCr_2Se_4 as a function of both $1/(T - \Theta)$ and H . Saturation is clearly seen in both the temperature dependence and the magnetic field dependence at $T = 200 \text{ K}$: on both plots $\Delta\nu$ levels off to give $A = 24 \pm 2 \text{ MHz}$.

This value of A gives a measure of the electron confinement around the muon at $T=200 \text{ K}$: assuming an expanded hydrogen-like MP wavefunction, the hyperfine coupling A scales as $1/R^3$, where R is the characteristic radius of the corresponding $1s$ electron wave function. We find $R \approx 0.3 \text{ nm}$, which falls between the nearest neighbor (NN) and next nearest neighbor (NNN) ion coordination spheres. This value of R is about an order of magnitude less than that calculated in [32] for temperature just above T_c . It is known, however, that R grows very fast as one approaches T_c from above [14, 21]. The value of the MP spin extracted from the slopes of both linear dependences of $\Delta\nu$ on T and H at higher temperature and lower magnetic field (see Fig. 4 and the inset for $T = 200 \text{ K}$) using Eq. (2) amounts to $\mathcal{S} = 30 \pm 4$. This is reasonably consistent with a fully polarized core of 4 NN and 12 NNN Cr^{3+} ions, yielding a net spin of

24, plus a partially ordered halo.

Here we find an important difference between MP in $4f$ and $3d$ MS: while in $4f$ MS the radius of the electron confinement is strongly “glued” to the corresponding NN coordination sphere [23, 24] because of the requirement of maximum electron overlap with extremely localized ($\sim 0.03 \text{ nm}$) $4f$ ion electrons, in $3d$ MS this requirement is much less stringent because of the significantly larger “spread” of the $3d$ wavefunction. In CdCr_2Se_4 , therefore, R falls in between the NN and NNN Cr^{3+} ions. More generally, exchange-driven electron localization in $3d$ magnets might enhance FM coupling between host magnetic ions by formation of MP around impurity atoms.

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